

FX509

PNP Epitaxial Planar Silicon Transistor

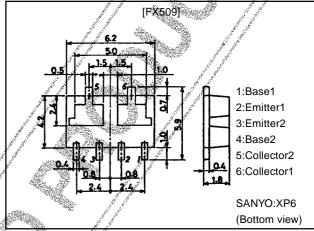
High-Current Switching Applications

Features

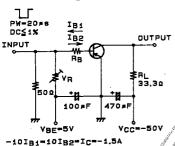
- · Composite type with 2PNP transistors contained in one package, facilitating high-density mounting.
- · The FX509 houses two chips, each being equivalent to the 2SB1215, in one package.
- · Matched pair characteristics.

Package Dimensions

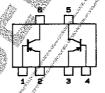
2118



Switching Time Test Circuit



Electrical Connection



- 1:Base1 2:Emitter1
- 3:Emitter2
- 4:Base2
- 5:Collector2
- 6:Collector1
- (Top view)

Specifications

Absolute Maximum Ratings at Ta = 25

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		-120	V
Collector-to-Emitter Voltage	^V ÇEO		-100	V
Emitter-to-Base Notage	√ ¥EBO		-6	V
Collector Current	√ lc		-3	Α
Collector Current (Pulse)	I _{CP}		-6	Α
Base Current	ΙB		-0.6	Α
Collector Dissipation	PC	Mounted on ceramic board (750mm ² ×0.8mm) 1unit	1.5	W
Total Dissipation	PT	Mounted on ceramic board (750mm ² ×0.8mm)	2	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

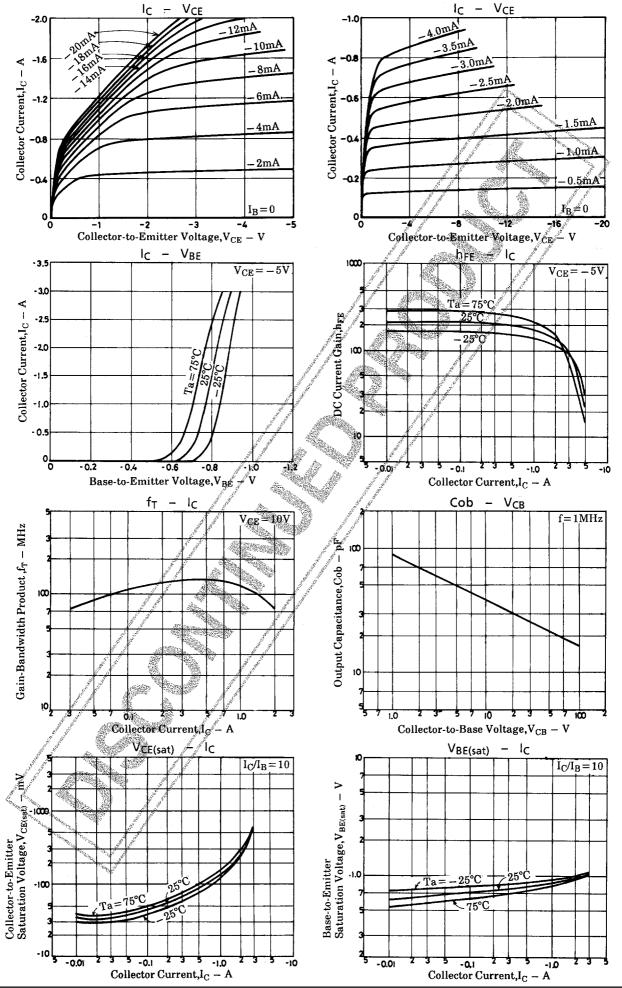
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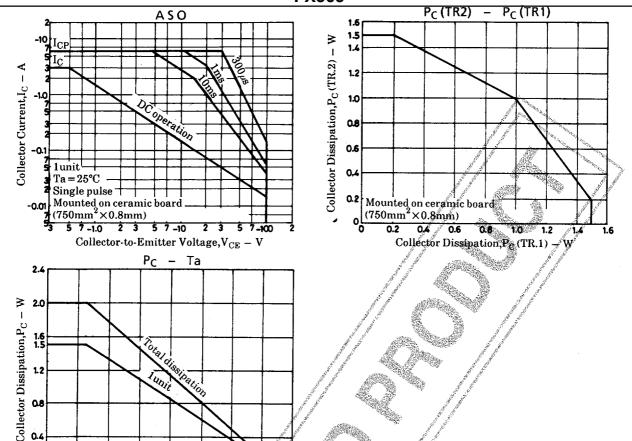
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Electrical Characteristics at Ta = 25 C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Uill
Collector Cutoff Current	I _{CBO}	V _{CB} =-100V, I _E =0	And the last	Neigh.	-1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0	and the same	A. A	-1	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =-5V, I _C =500mA	140	and the same of the	400	
	h _{FE} 2	V _{CE} =-5V, I _C =-2A	40		Market Market State	
DC Current Gain Ratio	hFE(small/ large)	V _{CE} =-5V, I _C =-500mA	0.8		Siller	
Gain-Bandwidth Product	fΤ	V _{CE} =-5V, I _C =-500mA	4800	180	John State of the	MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		4 0	11	pF
C-E Saturation Voltage	V _{CE(sat)}	I _C =-1.5A, I _B =-150mA	3/2	200	-500	mV
B-E Saturation Voltage	V _{BE(sat)}	I _C =-1.5A, I _B =-150mA		-0.9	<i>-</i> _1.2	V
C-B Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0	-120	J. J		V
C-E Breakdown Voltage	V(BR)CEO	I _C =–1mA, R _{BE} =∞	100			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-6	A ST		V
Turn-ON Time	t _{on}	See sepcified Test Circuit	gil.	100		ns
Storage Time	t _{stg}	See sepcified Test Circuit	selfer ell	800		ns
Fall Time	t _f	See sepcified Test Circuit	A STATE OF THE STA	50		ns



FX509



Mounted on ceramic board (750mm²×0.8mm)

60

40

80

Ambient Temperature, Ta - °C

100

120

140

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